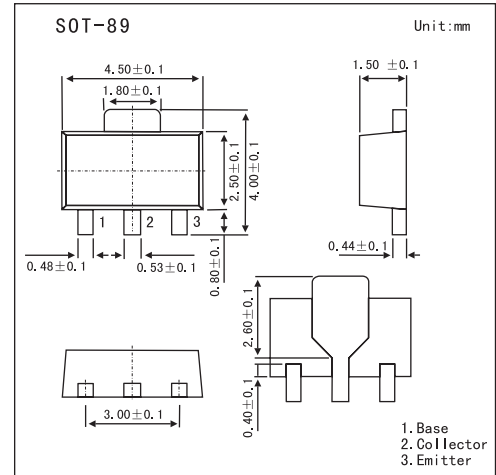


Low VCE(sat) Transistor

2SB1424

■ Features

- Low VCE(sat). VCE(sat) = -0.2V (Typ.) (IC/IB = -2A / -0.1A)
- Excellent DC current gain characteristics.
- PNP silicon transistor



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-20	V
Collector-emitter voltage	V _{CE0}	-20	V
Emitter-base voltage	V _{EB0}	-6	V
Collector current	I _C	-3	A
	I _{CP} *	-5	A
Collector dissipation	P _C	0.5	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Single pulse Pw=10ms.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C = -50μA	-20			V
Collector-emitter breakdown voltage	V _{CE0}	I _C = -1mA	-20			V
Emitter-base breakdown voltage	V _{EB0}	I _E = -50μA	-6			V
Collector cutoff current	I _{CB0}	V _{CB} = -20V			-0.1	μA
Emitter cutoff current	I _{EB0}	V _{EB} = -5V			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C = -0.1A	120		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C /I _B = -2A/ -0.1A			-0.5	V
Output capacitance	C _{ob}	V _{CB} = -10V, I _E =0A, f=1MHz		35		pF
Transition frequency	f _T	V _{CE} = -2V, I _E =0.5A, f=100MHz		240		MHz

■ hFE Classification

Marking	AEQ	AER
Rank	Q	R
hFE	120~270	180~390